Hyun Wook Shin

List of Publications by Year
in descending order

20 papers	136 citations	1683354 5 h-index	1281420 11 g-index
20 all docs	20 docs citations	20 times ranked	249 citing authors

#	Article	IF	Citations
1	Imprinted hysteresis loops and size-reduced ferroelectric polarization nanodots in epitaxial PbTiO3 thin film after heat treatment. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 2022, 276, 115533.	1.7	1
2	Ferroelectric switching and current characteristics dependence on ferroelectric polarization direction of microwave synthesized BiFeO3 nanocubes. Ceramics International, 2022, 48, 22712-22717.	2.3	1
3	Current change due to artificial patterning of the number of ferroelectric domain walls and nonvolatile memory characteristics. Applied Physics Letters, 2021, 119, 122901.	1.5	3
4	Nonvolatile-memory current characteristics of BiFeO3 nanodots switched by applying external bias and force. Ceramics International, 2021, 47, 28449-28454.	2.3	3
5	Preferential growth characteristics and ferroelectric properties of epitaxial SrBi2Nb2O9 thin films along the a-axis direction due to the misfit strains. Materials Science in Semiconductor Processing, 2021, 134, 105991.	1.9	2
6	Multiferroic and photovoltaic current properties of tetragonally strained BiFeO3 thin films. Journal of Electroceramics, 2020, 44, 242-247.	0.8	5
7	Ferroelectric properties of HfO2 nanodots with a diameter smaller than 10â€‰nm deposited on an ITO bottom electrode. Applied Physics Letters, 2020, 117, .	1.5	9
8	A conducting atomic force microscopy study of conducting filament nanobits in the epitaxial NiO thin film prepared precisely controlled by the oxidation time of the single crystalline Ni substrates. Ultramicroscopy, 2019, 205, 57-61.	0.8	4
9	Enhanced multiferroic properties of tetragonally strained epitaxial BiMnO3 thin films grown on single crystal Rh substrates. Solid State Sciences, 2019, 91, 7-9.	1.5	4
10	Characteristics of MoS2 monolayer non-volatile memory field effect transistors affected by the ferroelectric properties of BiFeO3 thin films with Pt and SrRuO3 bottom electrodes grown on glass substrates. Journal of Alloys and Compounds, 2019, 792, 673-678.	2.8	7
11	Characteristics of ferroelectric field effect transistors composed of a ferroelectric Bi3TaTiO9 gate stack and a single-layer MoS2 channel. Applied Physics Letters, 2019, 115, 242902.	1.5	3
12	Ferroelectric properties and piezoresponse force micoroscopy study of Bi3TaTiO9 thin films. Ultramicroscopy, 2019, 196, 49-53.	0.8	5
13	Cu-Doped ZnO Thin Films Grown by Co-deposition Using Pulsed Laser Deposition for ZnO and Radio Frequency Sputtering for Cu. Journal of Electronic Materials, 2018, 47, 4610-4614.	1.0	2
14	Ferroelectric properties of highly a-oriented polycrystalline Bi4Ti3O12 thin films grown on glass substrates. Journal of Materials Science: Materials in Electronics, 2018, 29, 2573-2576.	1.1	4
15	Nonvolatile ferroelectric memory based on PbTiO3 gated single-layer MoS2 field-effect transistor. Electronic Materials Letters, 2018, 14, 59-63.	1.0	17
16	Vortex ferromagnetic domain structures of ferromagnetic CoFe2O4 nanodisks formed by local crystallization using a heated atomic force microscope tip. Materials Letters, 2018, 213, 331-334.	1.3	3
17	Ferroelectric BiFeO3 nanodots formed in non-crystallized BiFeO3 thin-films via a local heating process using a heated atomic force microscope tip. Journal of Sol-Gel Science and Technology, 2018, 86, 170-174.	1.1	4
18	Phosphorene field-effect transistors using high-k gate dielectrics of epitaxial SrTiO 3 layers grown on Nb-doped SrTiO 3 substrates. Materials Science in Semiconductor Processing, 2017, 71, 409-412.	1.9	1

#	Article	IF	Citations
19	Large ferroelectric domain structures of epitaxial Bi2FeMnO6 thin films on Nb-doped SrTiO3 substrates. Journal of Materials Science: Materials in Electronics, 2017, 28, 15302-15305.	1.1	4
20	Short-wavelength infrared photodetector on Si employing strain-induced growth of very tall InAs nanowire arrays. Scientific Reports, 2015, 5, 10764.	1.6	54